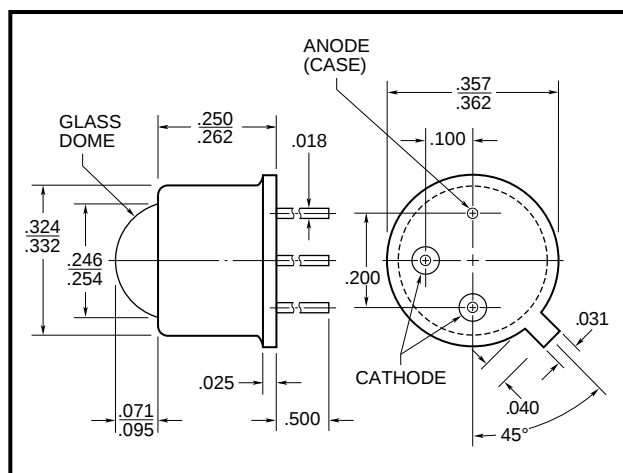




FEATURES

- Ultra high power output
- Four wire bonds on die corners
- Very narrow optical beam
- Standard 3-lead TO-39 hermetic package
- Chip size .030 x .030 inches

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified. Two cathode pins ***must be*** externally connected together.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	$I_F = 500\text{mA}$ $I_F = 10\text{A}$	40	50 600		mW
Radiant Intensity, I_e	$I_F = 500\text{mA}$		500		mW/sr
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Half Intensity Beam Angle, θ			7		Deg
Forward Voltage, V_F	$I_F = 500\text{mA}$		1.65	2	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		90		pF
Rise Time			0.7		μsec
Fall Time			0.7		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation ¹	1000mW
Continuous Forward Current	500mA
Peak Forward Current (10 μs , 400Hz) ²	10A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	240°C

¹Derate per Thermal Derating Curve above 25°C

²Derate linearly above 25°C

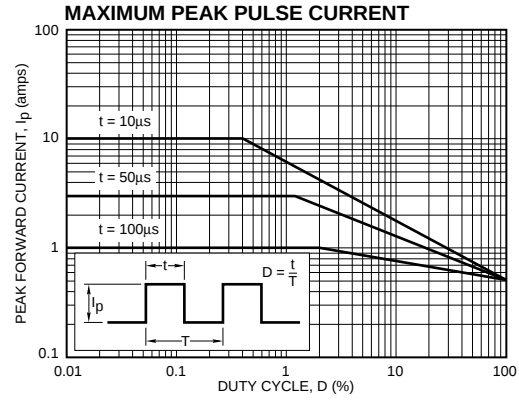
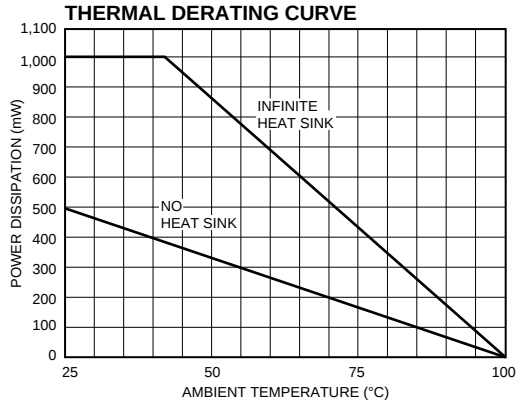
THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C to 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R_{THJA} ¹	150°C/W Typical
Thermal Resistance, R_{THJA} ²	60°C/W Typical

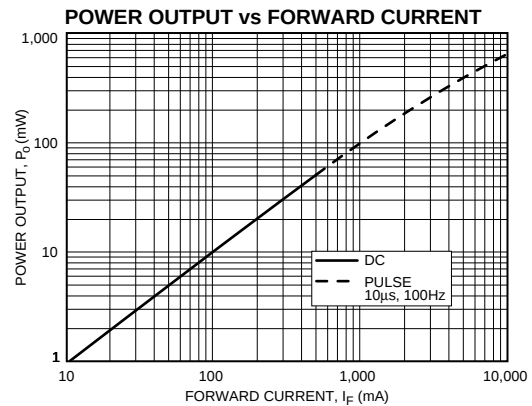
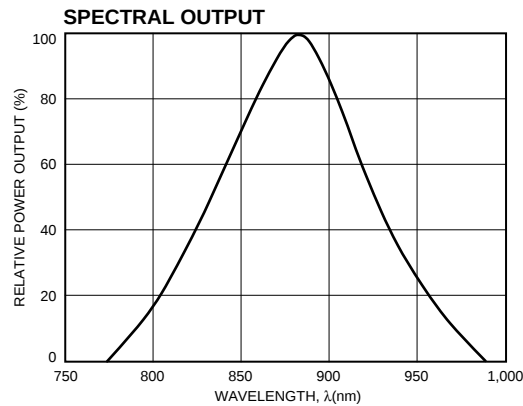
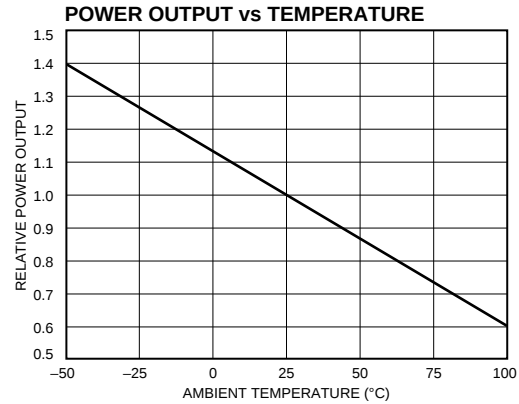
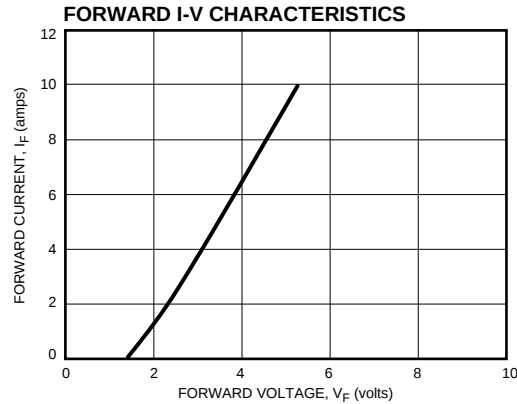
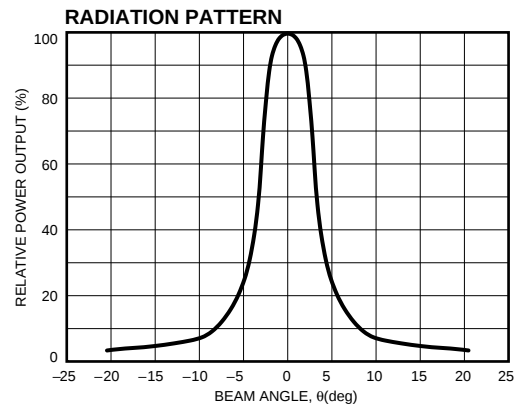
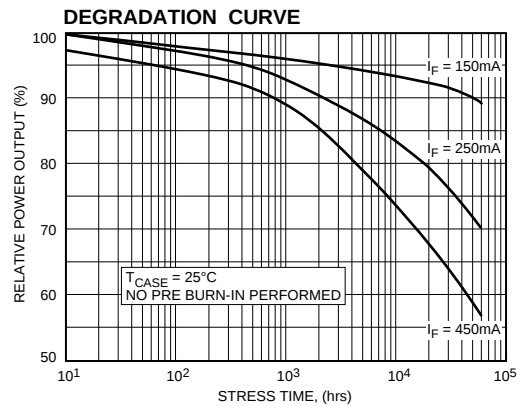
¹Heat transfer minimized by measuring in still air with minimum heat conducting through leads

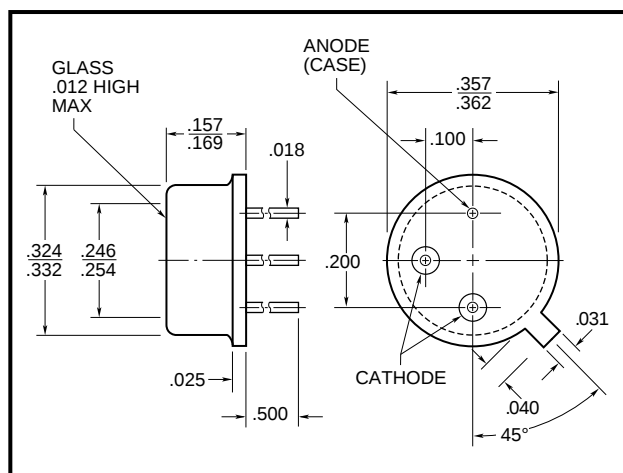
²Air circulating at a rapid rate to keep case temperature at 25°C

MAXIMUM RATINGS



TYPICAL CHARACTERISTICS





FEATURES

- Ultra high power output
- Four wire bonds on die corners
- Very uniform optical beam
- Standard 3-lead TO-39 hermetic package
- Chip size .030 x .030 inches

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified. Two cathode pins **must be** externally connected together.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	$I_F = 500\text{mA}$ $I_F = 10\text{A}$	60	75 1000		mW
Radiant Intensity, I_e	$I_F = 500\text{mA}$		60		mW/sr
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Half Intensity Beam Angle, θ			110		Deg
Forward Voltage, V_F	$I_F = 500\text{mA}$		1.65	2	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		90		pF
Rise Time			0.7		μsec
Fall Time			0.7		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation ¹	1000mW
Continuous Forward Current	500mA
Peak Forward Current (10 μs , 400Hz) ²	10A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	240°C

¹Derate per Thermal Derating Curve above 25°C

²Derate linearly above 25°C

THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C to 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R_{THJA} ¹	145°C/W Typical
Thermal Resistance, R_{THJA} ²	75°C/W Typical

¹Heat transfer minimized by measuring in still air with minimum heat conducting through leads

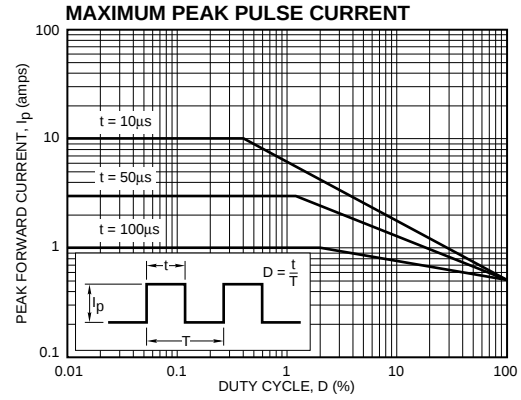
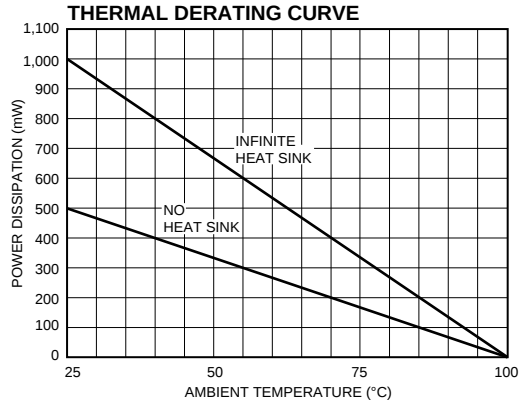
²Air circulating at a rapid rate to keep case temperature at 25°C



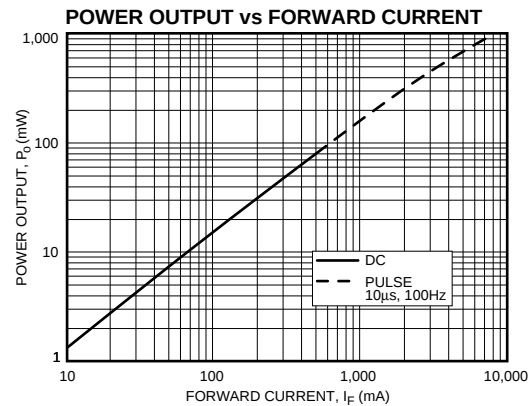
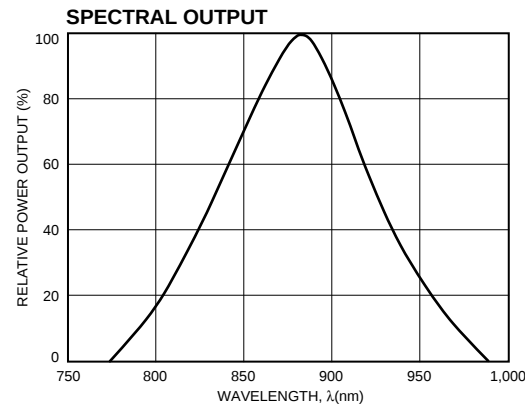
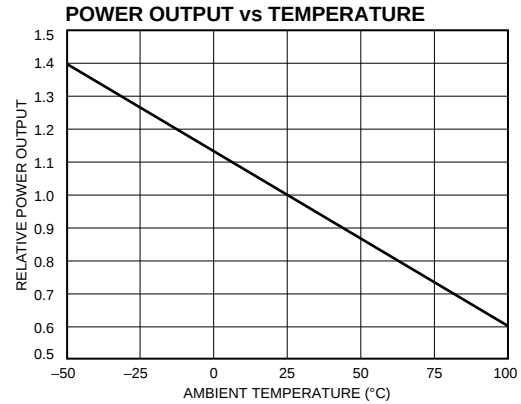
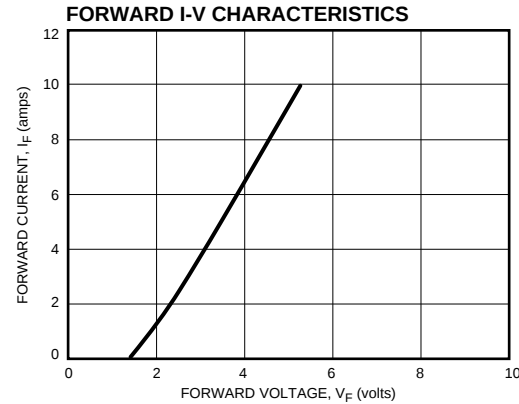
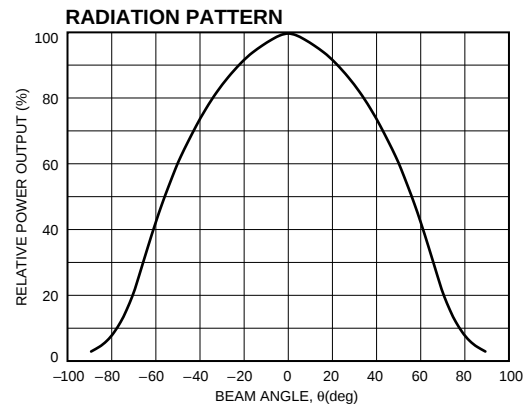
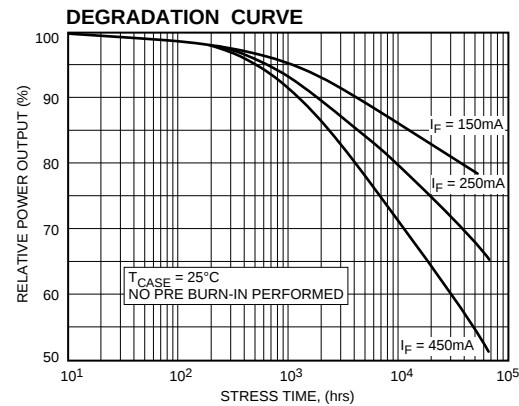
OPTO DIODE CORP.

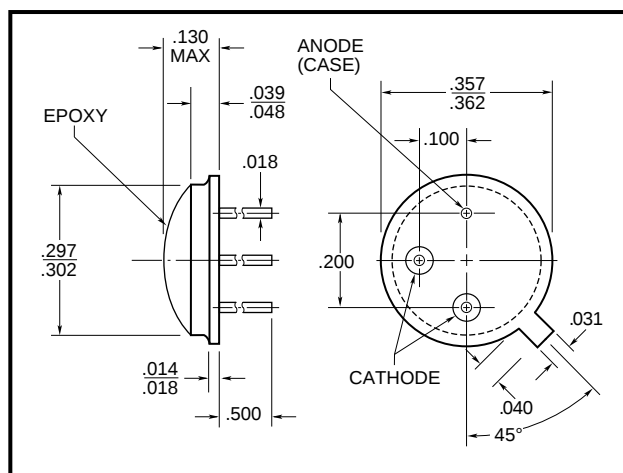
750 Mitchell Road, Newbury Park, California 91320
Phone (805) 499-0335 FAX (805) 499-8108

MAXIMUM RATINGS



TYPICAL CHARACTERISTICS





FEATURES

- Ultra high power output
- Four wire bonds on die corners
- Very uniform optical beam
- Standard 3-lead TO-39 hermetic package
- Chip size .030 x .030 inches

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ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	$I_F = 500\text{mA}$ $I_F = 10\text{A}$	80	100 1300		mW
Radiant Intensity, I_e	$I_F = 500\text{mA}$		60		mW/sr
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Half Intensity Beam Angle, θ			110		Deg
Forward Voltage, V_F	$I_F = 500\text{mA}$		1.65	2	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		90		pF
Rise Time			0.7		μsec
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ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation ¹	1000 mW
Continuous Forward Current	500mA
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Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	240°C

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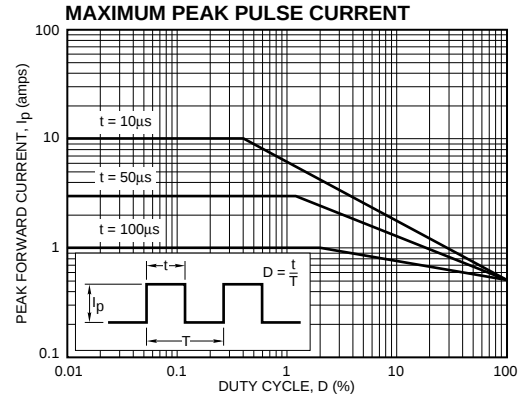
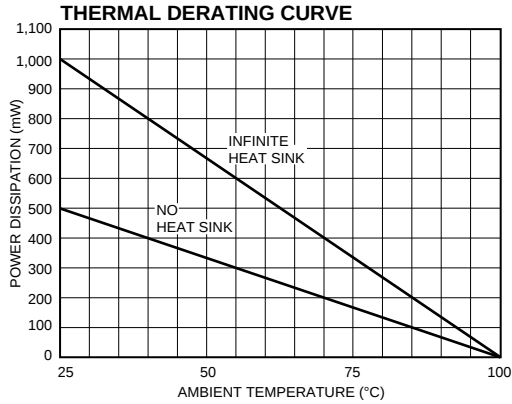
²Air circulating at a rapid rate to keep case temperature at 25°C



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MAXIMUM RATINGS



TYPICAL CHARACTERISTICS

